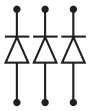
CMKD4448

SURFACE MOUNT
TRIPLE ISOLATED
HIGH SPEED SILICON
SWITCHING DIODES

ULTRAmini™



SOT-363 CASE

Central Semiconductor Corp.

www.centralsemi.com

DESCRIPTION:

The CENTRAL SEMICONDUCTOR CMKD4448 type contains three (3) Isolated High Speed Silicon Switching Diodes, manufactured by the epitaxial planar process, epoxy molded in an ULTRAmini™ surface mount package, designed for applications requiring high speed switching applications.

MARKING CODE: K48

MAXIMUM RATINGS: (T_A=25°C)	**SYMBOL**		**UNITS**
Continuous Reverse Voltage	V_R	75	V
Peak Repetitive Reverse Voltage	V_{RRM}	100	V
Continuous Forward Current	I_F	250	mA
Peak Repetitive Forward Current	I_{FRM}	500	mA
Peak Forward Surge Current, tp=1.0μs	I_{FSM}	4.0	A
Peak Forward Surge Current, tp=1.0s	I_{FSM}	1.0	A
Power Dissipation	P_D	325	mW
Operating and Storage Junction Temperature	T_J, T_{stg}	-65 to +150	°C
Thermal Resistance	Θ_{JA}	385	°C/W

ELECTRICAL CHARACTERISTICS PER DIODE: (T_A=25°C unless otherwise noted)

SYMBOL	**TEST CONDITIONS**	**MIN**	**MAX**	**UNITS**
I_R	V_R=20V		25	nA
BV_R	I_R=5.0μA	75		V
BV_R	I_R=100μA	100		V
V_F	I_F=100mA		1.0	V
C_T	V_R=0, f=1.0MHz		4.0	pF
t_{rr}	I_R=I_F=10mA, R_L=100Ω Rec. to 1.0mA		4.0	ns

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HIGH SPEED SILICON
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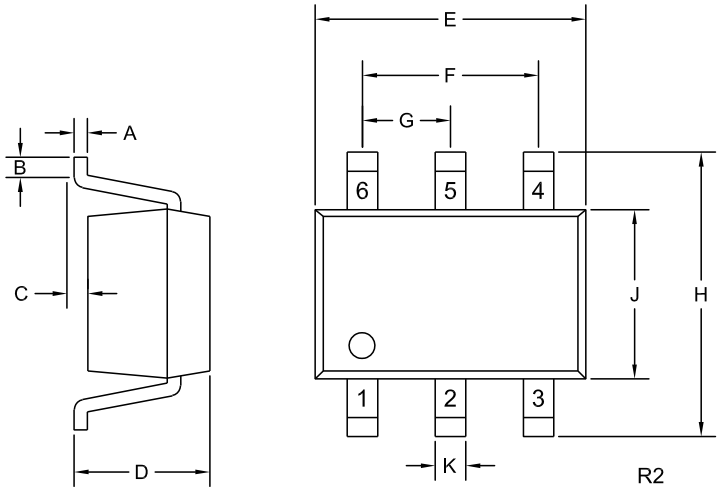
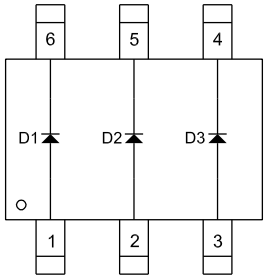
SOT-363 CASE - MECHANICAL OUTLINE



PIN CONFIGURATION



DIMENSIONS				
	INCHES		MILLIMETERS	
SYMBOL	MIN	MAX	MIN	MAX
A	0.004	0.010	0.10	0.25
B	0.005	-	0.12	-
C	0.000	0.004	0.00	0.10
D	0.031	0.043	0.80	1.10
E	0.071	0.087	1.80	2.20
F	0.051		1.30	
G	0.026		0.65	
H	0.075	0.091	1.90	2.30
J	0.043	0.055	1.10	1.40
K	0.006	0.012	0.15	0.30

SOT-363 (REV: R2)

LEAD CODE:
1) Anode D1
2) Anode D2
3) Anode D3
4) Cathode D3
5) Cathode D2
6) Cathode D1

MARKING CODE: K48

R5 (13-January 2010)